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				Application Number	10/774,406	
1	INFORMATION DIS	SCLOS	URE	Filing Date	2/10/2004	
	STATEMENT BY A	APPLIC	ANT	First Named Inventor	Y. TANABE, et al.	
				Art Unit	2813	
	luca se manu chaate se	e <i>погаеезт</i>	v)	Examiner Name	Thanhha S. PHAM	
Sheet	1	of	2	Attorney Docket Number	501.37465CC8	
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			U.S. PATENT	DOCUMENTS	
Examiner Initials'	Cite No.1	Document Number  Number-Kind Code <sup>3</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TSP		US- 4,376,796	03-15-83	Arrasmith et al.	
748		US- 4,139,858	02-13-79	Cohen et al.	
		US-			
-		US-			
			FOREIGN DATES	TOOLING	
<del></del>			FOREIGN PATEN	II DOCUMENTS	Pages, Columns, Lines

FOREIGN PATENT DOCUMENTS								
Examiner Initials'	Cite No.1	Foreign Patent Document  Country Code <sup>3</sup> -Number <sup>4</sup> -Nnd Code <sup>5</sup> (ff known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T⁰		
13		0 671 761 A1	09-13-95	Tadahiro OHMI				
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Examiner Signature		Date Considered	9/6/03

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form			APR 0 4 200	S Com	plete if Known
			SET.	Application Number	10/774,406
INFO	<b>RMATIO</b>	N DISCL	OSURE	Filing Date	2/10/2004
		<b>BY APP</b>		First Named Inventor	Y. TANABE, et al.
				Group Art Unit	2813
	use as many s	heets as neces	sary)	Examiner Name	Thanhha s. PHAM
Sheet	2	of	2	Attorney Docket Number	501.37485CC8
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Examiner	Cite	NON PATENT LITERATURE DOCUMENTS  Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the	T <sup>2</sup>
Initials*	Cite, No.	item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
		KOOI E ET AL: "Formation of silicon nitride at a Si-Si02 interface during local oxidation of silicon and during heat-treatment of oxidized silicon in NH3 gas" JOURNAL OF THE ELECTROCHEMICAL SOCIETY USA, vo 123, no. 7, July 1976 (1976-07), pages 1117-1120.	
TSP		Supplementary Partial European Search Report for EP 98 90 5758 (completed Feb. 3, 2005).	
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Examiner '	Date	91 (11)
Signature	Considered	<u> </u>

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